



# 5STF 06D2020

Old part no. TR 907F-560-20

## Medium Frequency Thyristor

### Properties

- Amplifying gate
- High operational capability
- Optimized turn-on and turn-off parameters
- High operating frequency

### Applications

- Power switching applications

### Key Parameters

$V_{DRM}, V_{RRM}$	= 2 000	V
$I_{TAV}$	= 557	A
$I_{TSM}$	= 8.0	kA
$V_{TO}$	= 2.348	V
$r_T$	= 0.386	mΩ
$t_q$	= 20.0	μs

### Types

	$V_{RRM}, V_{DRM}$
5STF 06D2020	2 000 V
5STF 06D1820	1 800 V

Conditions:  
 $T_j = -40 \div 125$  °C, half sine waveform,  
 $f = 50$  Hz, note 1

### Mechanical Data

$F_m$	Mounting force	10 ± 2 kN
$m$	Weight	0.26 kg
$D_s$	Surface creepage distance	25 mm
$D_a$	Air strike distance	14 mm

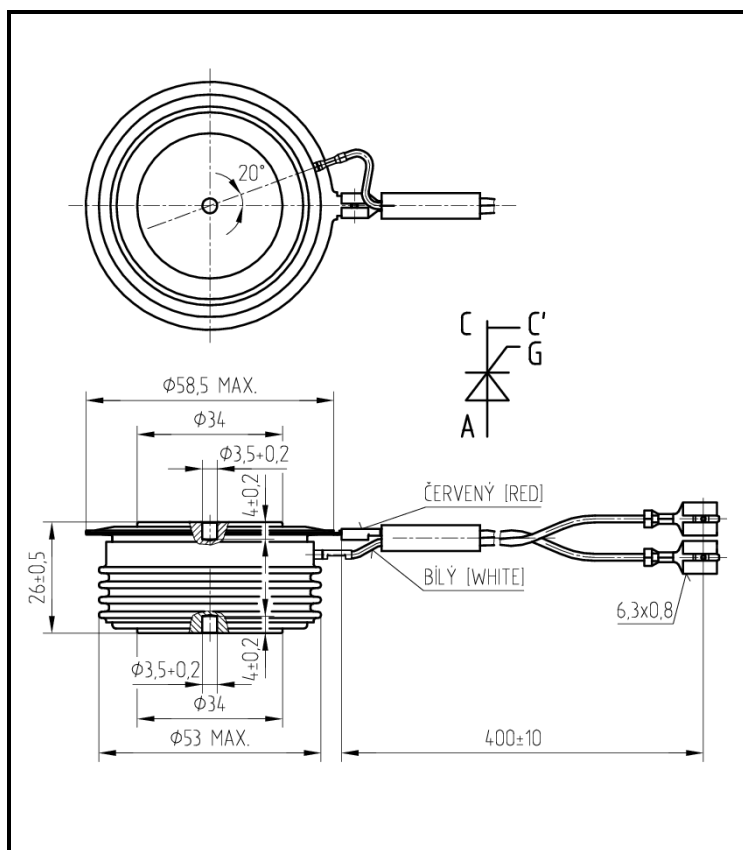


Fig. 1 Case



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<b>Maximum Ratings</b>			<b>Maximum Limits</b>	<b>Unit</b>
$V_{RRM}$ $V_{DRM}$	<b>Repetitive peak reverse and off-state voltage</b> $T_j = -40 \div 125 \text{ }^\circ\text{C}$ , note 1	<b>5STF 06D2020</b> <b>5STF 06D1820</b>	<b>2 000</b> <b>1 800</b>	<b>V</b>
$I_{TRMS}$	<b>RMS on-state current</b> $T_c = 70 \text{ }^\circ\text{C}$ , half sine waveform, $f = 50 \text{ Hz}$		<b>875</b>	<b>A</b>
$I_{TAVm}$	<b>Average on-state current</b> $T_c = 70 \text{ }^\circ\text{C}$ , half sine waveform, $f = 50 \text{ Hz}$		<b>557</b>	<b>A</b>
$I_{TSM}$	<b>Peak non-repetitive surge</b> half sine pulse, $V_R = 0 \text{ V}$	$t_p = 10 \text{ ms}$ $t_p = 8.3 \text{ ms}$	<b>8 000</b> <b>8 550</b>	<b>A</b>
$\int i^2 t$	<b>Limiting load integral</b> half sine pulse, $V_R = 0 \text{ V}$	$t_p = 10 \text{ ms}$ $t_p = 8.3 \text{ ms}$	<b>320 000</b> <b>303 000</b>	<b>A<sup>2</sup>s</b>
$(di_T/dt)_{cr}$	<b>Critical rate of rise of on-state current</b> $I_T = I_{TAVm}$ , half sine waveform, $f = 50 \text{ Hz}$ , $V_D = 2/3 V_{DRM}$ , $t_r = 0.3 \text{ } \mu\text{s}$ , $I_{GT} = 2 \text{ A}$		<b>800</b>	<b>A/<math>\mu\text{s}</math></b>
$(dv_D/dt)_{cr}$	<b>Critical rate of rise of off-state voltage</b> $V_D = 2/3 V_{DRM}$		<b>1 000</b>	<b>V/<math>\mu\text{s}</math></b>
$P_{GAVm}$	<b>Maximum average gate power losses</b>		<b>3</b>	<b>W</b>
$I_{FGM}$	<b>Peak gate current</b>		<b>10</b>	<b>A</b>
$V_{FGM}$	<b>Peak gate voltage</b>		<b>12</b>	<b>V</b>
$V_{RGM}$	<b>Reverse peak gate voltage</b>		<b>10</b>	<b>V</b>
$T_{jmin} - T_{jmax}$	<b>Operating temperature range</b>		<b>-40 <math>\div</math> 125</b>	<b><math>^\circ\text{C}</math></b>
$T_{stgmin}$ - $T_{stgmax}$	<b>Storage temperature range</b>		<b>-40 <math>\div</math> 125</b>	<b><math>^\circ\text{C}</math></b>

Unless otherwise specified  $T_j = 125 \text{ }^\circ\text{C}$

Note 1: De-rating factor of 0.13%  $V_{RRM}$  or  $V_{DRM}$  per  $^\circ\text{C}$  is applicable for  $T_j$  below  $25 \text{ }^\circ\text{C}$

Characteristics		Value			Unit
		min.	typ.	max.	
$V_{TM}$	<b>Maximum peak on-state voltage</b> $I_{TM} = 1\ 500\ A$			<b>2.930</b>	V
$V_{T0}$	<b>Threshold voltage</b>			<b>2.348</b>	V
$r_T$	<b>Slope resistance</b> $I_{T1} = 880\ A, I_{T2} = 2\ 639\ A$			<b>0.386</b>	mΩ
$I_{DM}$	<b>Peak off-state current</b> $V_D = V_{DRM}$			<b>70</b>	mA
$I_{RM}$	<b>Peak reverse current</b> $V_R = V_{RRM}$			<b>70</b>	mA
$t_{gd}$	<b>Delay time</b> $T_j = 25\ ^\circ C, V_D = 0.4\ V_{DRM}, I_{TM} = I_{TAVM},$ $t_r = 0.3\ \mu s, I_{GT} = 2\ A$			<b>2.0</b>	μs
$t_{q1}$	<b>Turn-off time</b> $I_T = 500\ A, di_T/dt = -50\ A/\mu s, V_R = 100\ V, V_D = 2/3\ V_{DRM},$ $dv_D/dt = 50\ V/\mu s$			<b>20.0</b>	μs
$Q_{rr}$	<b>Recovery charge</b> <i>the same conditions as at <math>t_{q1}</math></i>			<b>240</b>	μC
$I_{rrM}$	<b>Reverse recovery current</b> <i>the same conditions as at <math>t_{q1}</math></i>			<b>80</b>	A
$I_H$	<b>Holding current</b>	$T_j = 25\ ^\circ C$ $T_j = 125\ ^\circ C$		<b>250</b> <b>150</b>	mA
$I_L$	<b>Latching current</b>	$T_j = 25\ ^\circ C$ $T_j = 125\ ^\circ C$		<b>1\ 500</b> <b>1\ 000</b>	mA
$V_{GT}$	<b>Gate trigger voltage</b> $V_D = 12\ V, I_T = 4\ A$	$T_j = -40\ ^\circ C$ $T_j = 25\ ^\circ C$ $T_j = 125\ ^\circ C$	<b>0.25</b>	<b>4</b> <b>3</b> <b>2</b>	V
$I_{GT}$	<b>Gate trigger current</b> $V_D = 12\ V, I_T = 4\ A$	$T_j = -40\ ^\circ C$ $T_j = 25\ ^\circ C$ $T_j = 125\ ^\circ C$	<b>10</b>	<b>1000</b> <b>500</b> <b>300</b>	mA

Unless otherwise specified  $T_j = 125\ ^\circ C$

<b>Thermal Parameters</b>		<b>Value</b>	<b>Unit</b>
$R_{thjc}$	<b>Thermal resistance junction to case</b> <i>double side cooling</i>	<b>32.0</b>	<b>K/kW</b>
	<i>anode side cooling</i>	<b>52.0</b>	
	<i>cathode side cooling</i>	<b>83.0</b>	
$R_{thch}$	<b>Thermal resistance case to heatsink</b> <i>double side cooling</i>	<b>10.0</b>	<b>K/kW</b>
	<i>single side cooling</i>	<b>20.0</b>	

<b>Transient Thermal Impedance</b>						
<b>Analytical function for transient thermal impedance</b> $Z_{thjc} = \sum_{i=1}^5 R_i (1 - \exp(-t/\tau_i))$	$i$	1	2	3	4	5
	$\tau_i$ (s)	0.4857	0.2162	0.0762	0.0043	0.0006
	$R_i$ (K/kW)	13.07	8.03	8.20	2.57	0.13
Conditions: $F_m = 10 \pm 2$ kN, Double side cooled						
<b>Correction for periodic waveforms</b> 180° sine: add 2.3 K/kW 180° rectangular: add 3.1 K/kW 120° rectangular: add 5.2 K/kW 60° rectangular: add 8.7 K/kW						
<b>Fig. 2</b> Dependence transient thermal impedance junction to case on square pulse						

**On-State Characteristics**

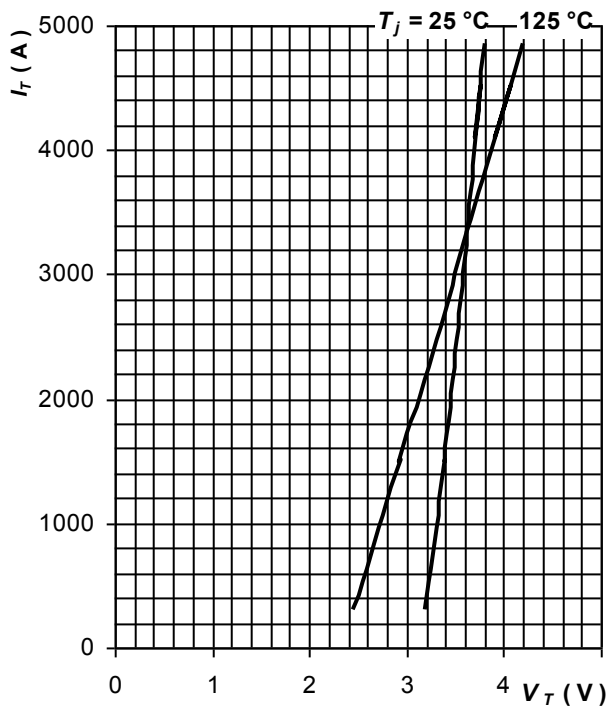


Fig. 3 Maximum on-state characteristics

**Gate Trigger Characteristics**

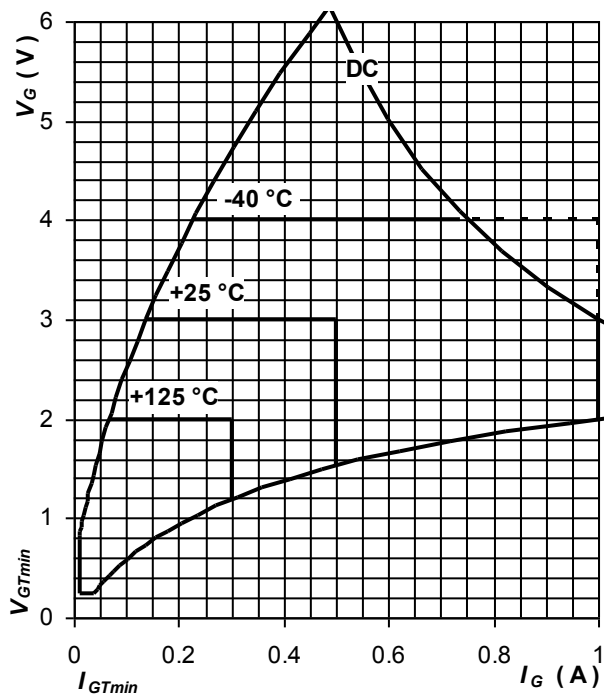


Fig. 4 Gate trigger characteristics

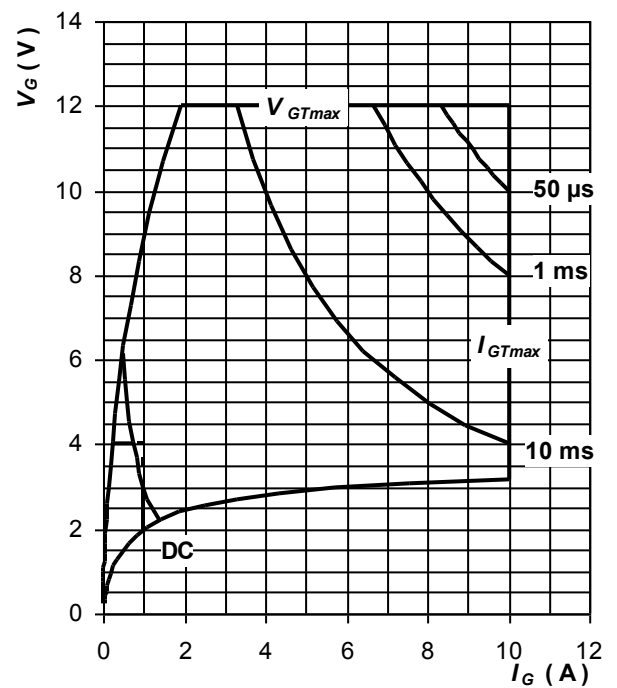


Fig. 5 Maximum peak gate power loss

## Surge Characteristics

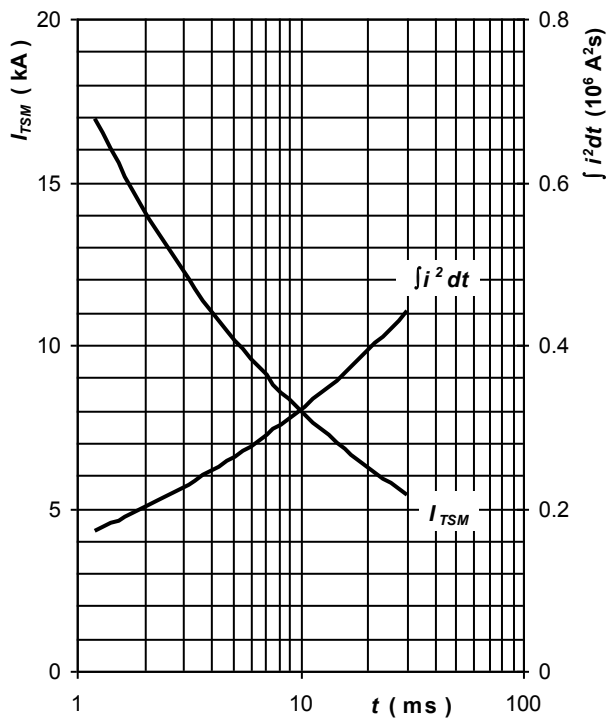


Fig. 6 Surge on-state current vs. pulse length, half sine wave, single pulse,  $V_R = 0 \text{ V}$ ,  $T_j = T_{jmax}$

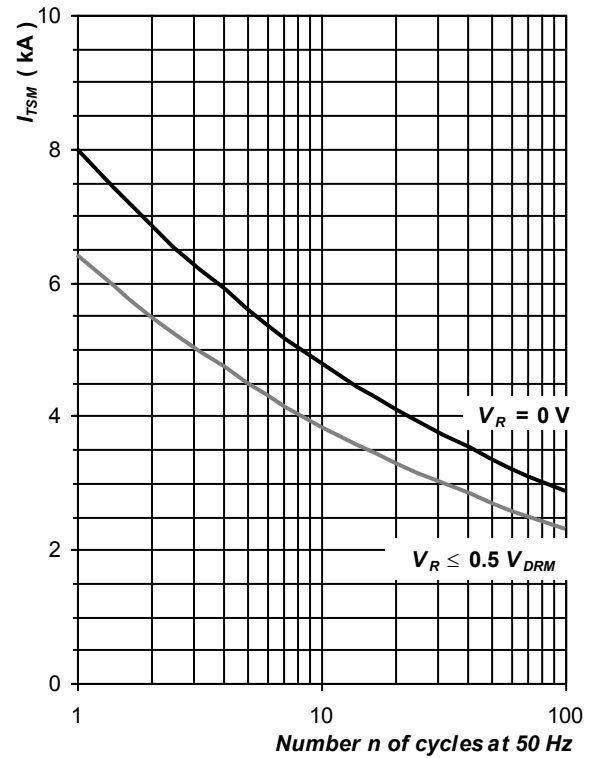


Fig. 7 Surge on-state current vs. number of pulses, half sine wave,  $T_j = T_{jmax}$

**Power Loss and Maximum Case Temperature Characteristics**

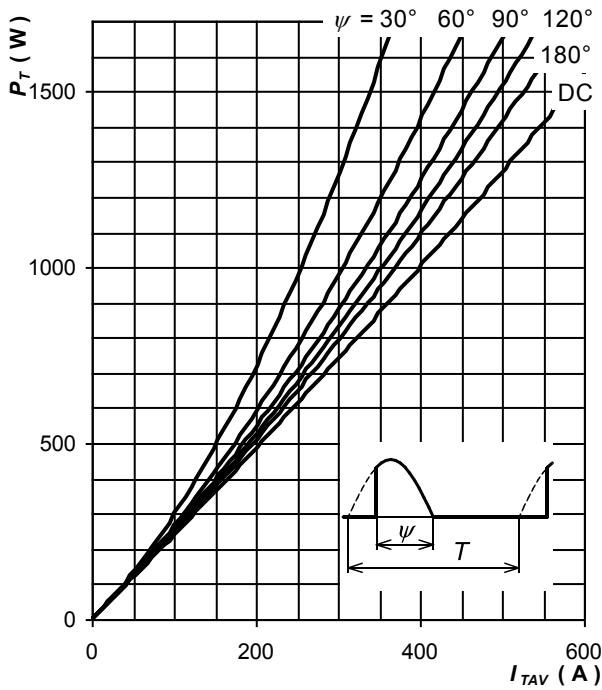


Fig. 8 On-state power loss vs. average on-state current, sine waveform,  $f = 50 \text{ Hz}$ ,  $T = 1/f$

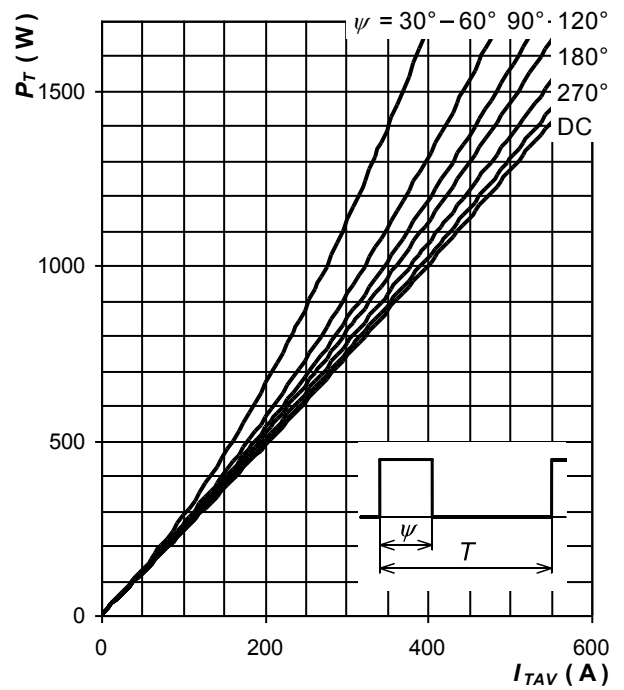


Fig. 9 On-state power loss vs. average on-state current, square waveform,  $f = 50 \text{ Hz}$ ,  $T = 1/f$

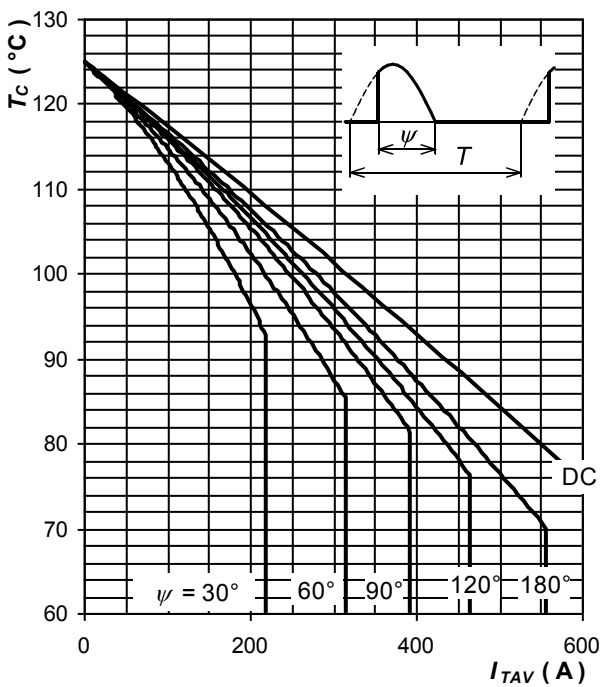


Fig. 10 Max. case temperature vs. aver. on-state current, sine waveform,  $f = 50 \text{ Hz}$ ,  $T = 1/f$

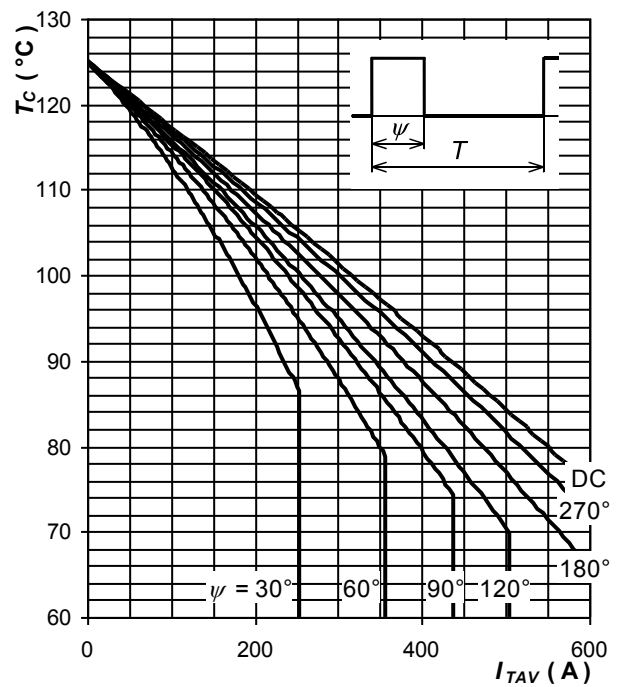


Fig. 11 Max. case temperature vs. aver. on-state current, square waveform,  $f = 50 \text{ Hz}$ ,  $T = 1/f$

Note 2: Figures number 8 ÷ 11 have been calculated without considering any turn-on and turn-off losses. They are valid for  $f = 50$  or  $60 \text{ Hz}$  operation.

**Turn-off Time, Parameter Relationship**

Maximum values of turn-off time at application specific conditions are given by using this formula:

$$t_q = t_{q1} \cdot \frac{t_q(T_j)}{t_{q1}} \cdot \frac{t_q(dv_D/dt)}{t_{q1}} \cdot \frac{t_q(-di_T/dt)}{t_{q1}}$$

where:

$t_{q1}$  is turn-off time at standard conditions, see section "Characteristics"

$\frac{t_q(T_j)}{t_{q1}}$  is factor to be taken from fig. 12

$\frac{t_q(dv_D/dt)}{t_{q1}}$  is factor to be taken from fig. 13

$\frac{t_q(-di_T/dt)}{t_{q1}}$  is factor to be taken from fig. 14

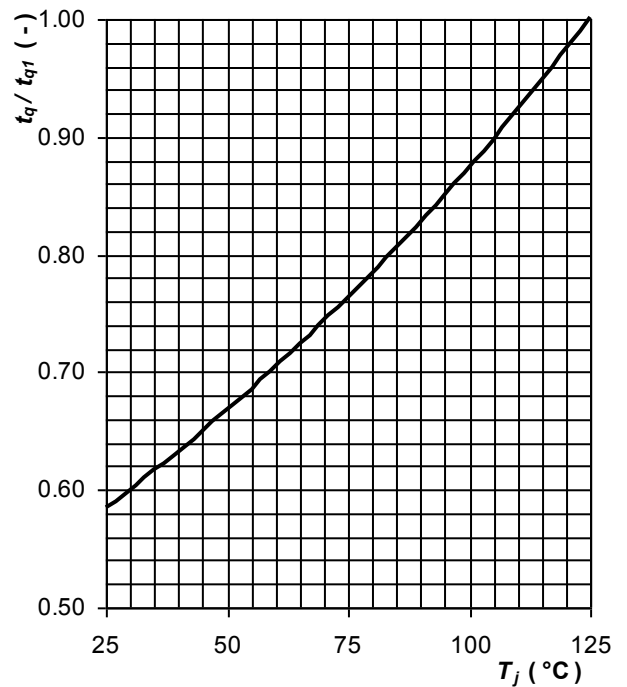


Fig. 12 Normalised maximum turn-off time vs. junction temperature

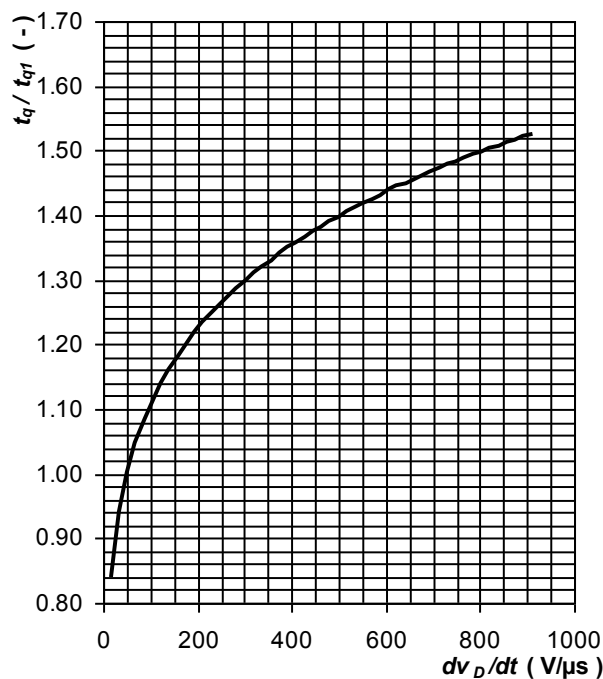


Fig. 13 Normalised maximum turn-off time vs. rate of rise of off-state voltage

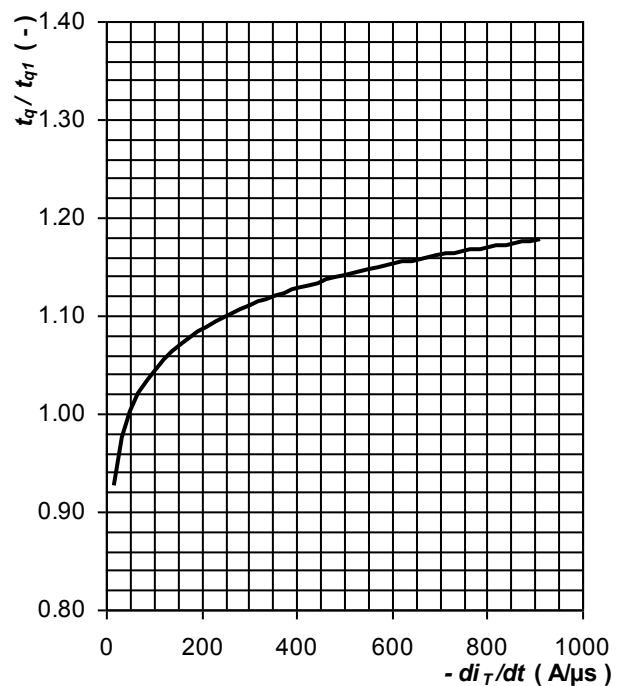


Fig. 14 Normalised maximum turn-off time vs. rate of fall of on-state current

**Turn-on Characteristics**

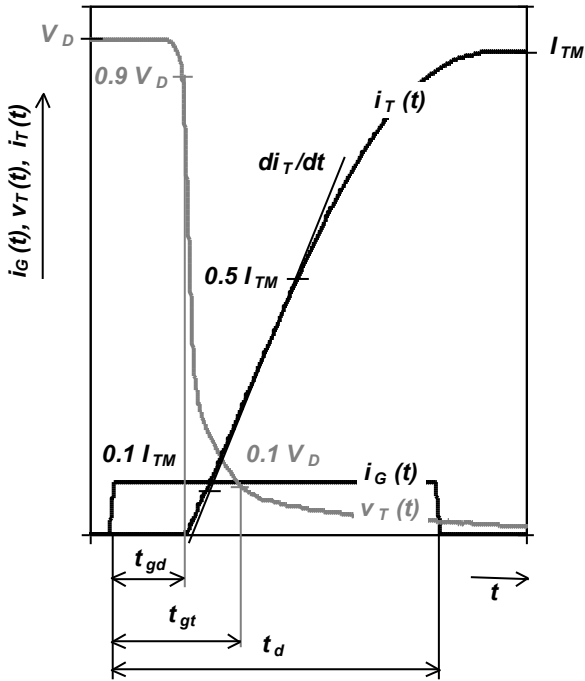


Fig. 15 Typical waveforms and definition of symbols at turn-on of a thyristor

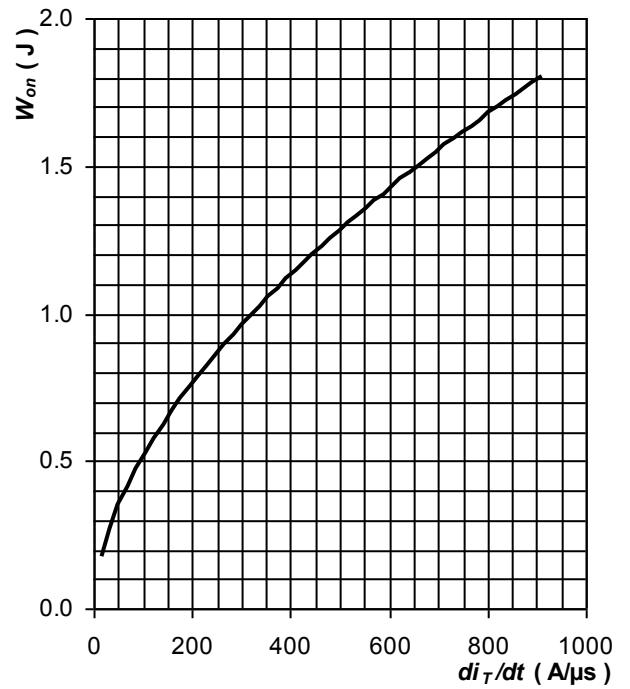


Fig. 16 Maximum turn-on energy per pulse vs. rate of rise on-state current,  $T_j = T_{jmax}$

**Turn-off Characteristics**

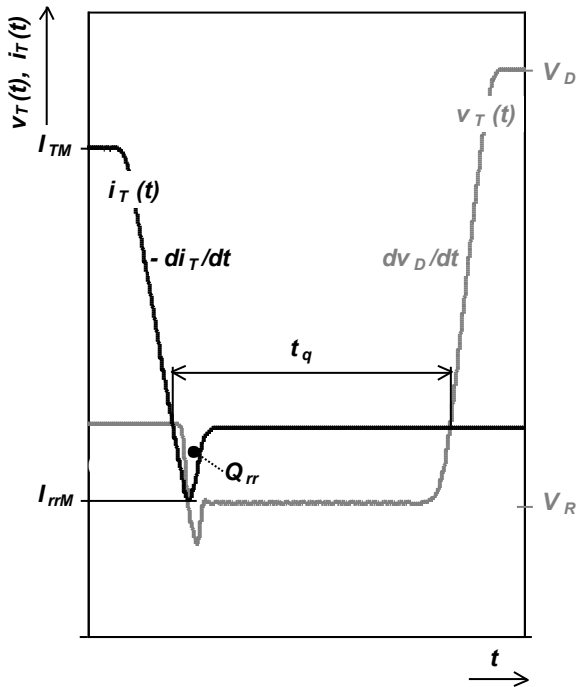


Fig. 17 Typical waveforms and definition of symbols at turn-off of a thyristor, inductive switching without RC snubber

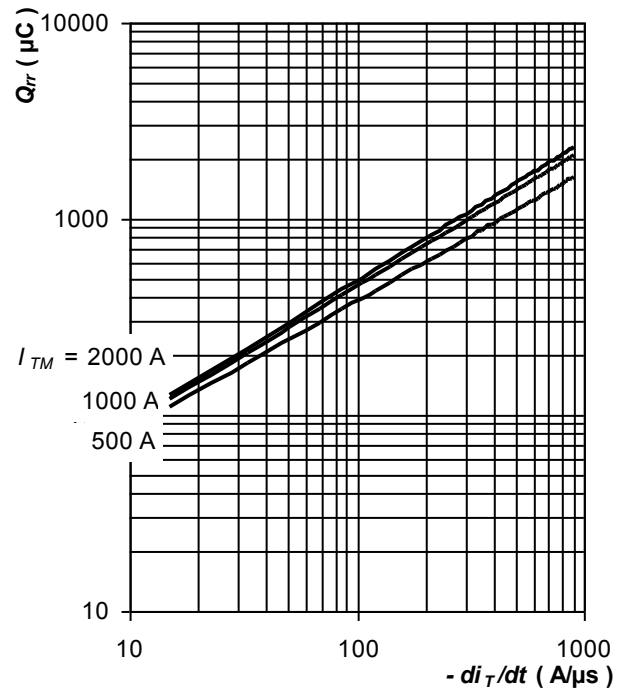


Fig. 18 Max. recovered charge vs. rate of fall on-state current, trapezoid pulse,  $V_R = 100 \text{ V}$ ,  $T_j = T_{jmax}$

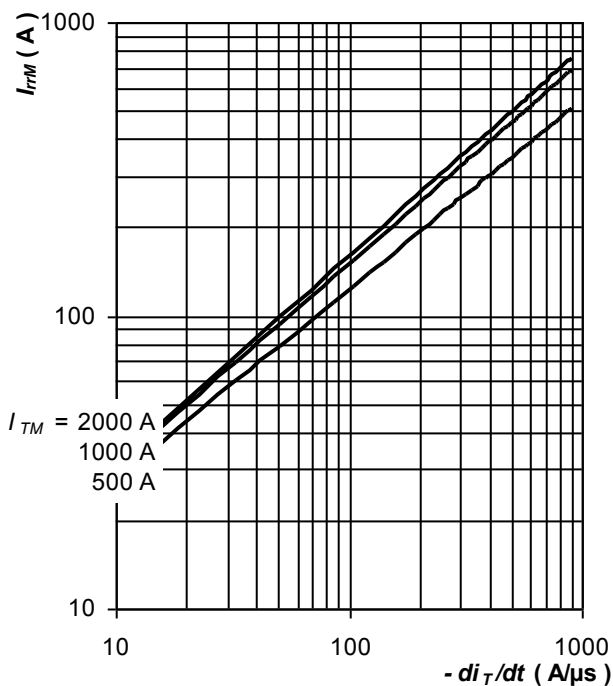


Fig. 19 Max. reverse recovery current vs. rate of fall on-state current, trapezoid pulse,  $V_R = 100 \text{ V}$ ,  $T_j = T_{jmax}$

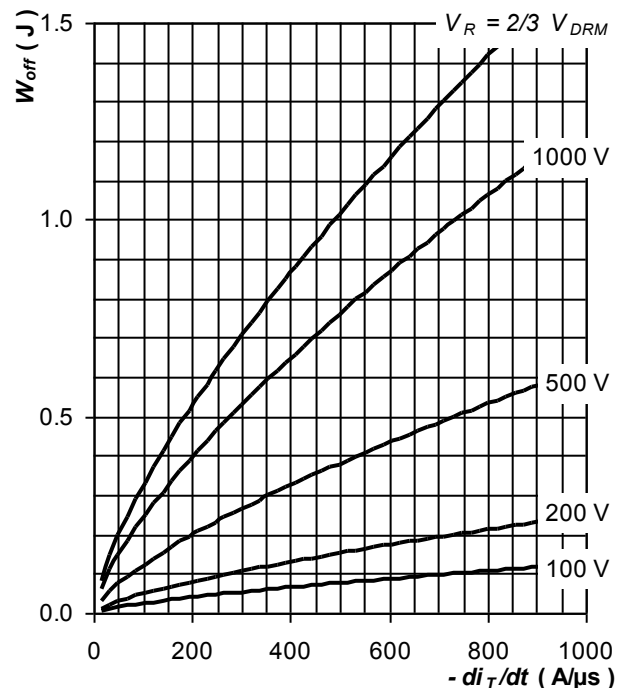


Fig. 20 Maximum turn-off energy per pulse vs. rate of fall on-state current, trapezoid pulse, inductive switching without RC snubber,  $I_{TM} = 2\ 000 \text{ A}$ ,  $T_j = T_{jmax}$

**Frequency Ratings**

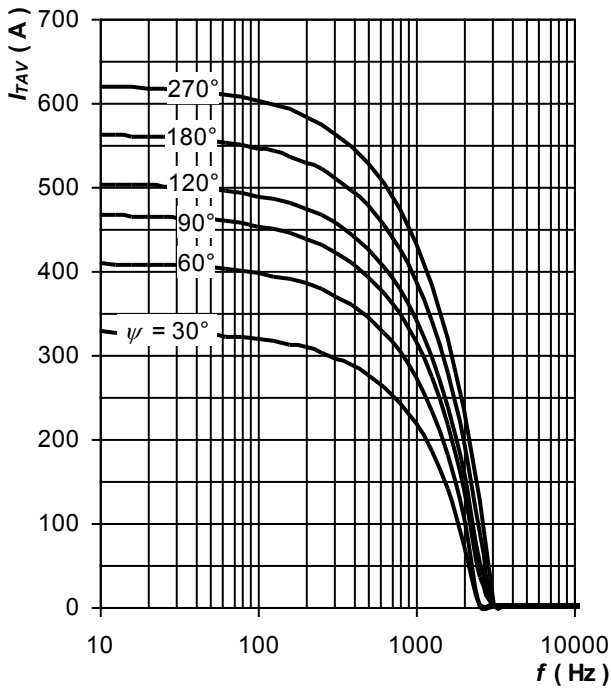


Fig. 21 Average on-state current vs. frequency, trapezoid waveform,  $T_C = 70^\circ\text{C}$ ,  $di_T/dt = \pm 100\text{ A}/\mu\text{s}$ ,  $V_R = 100\text{ V}$

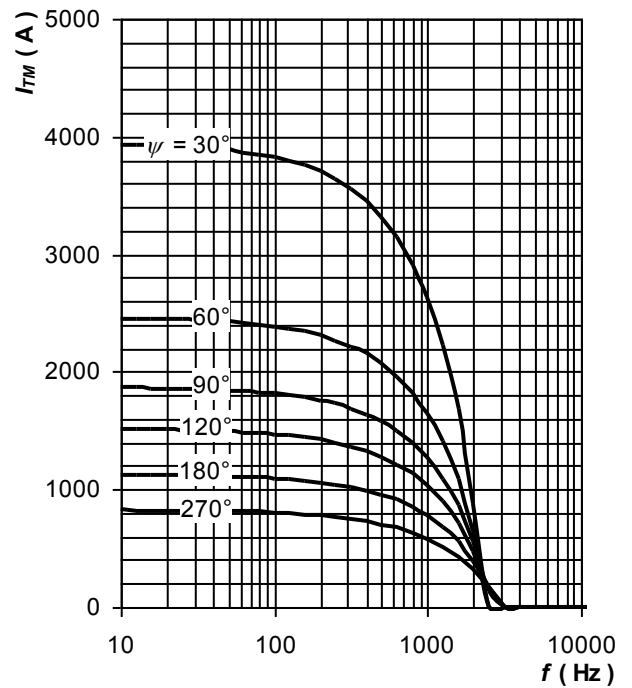


Fig. 22 Maximum on-state current vs. frequency, trapezoid waveform,  $T_C = 70^\circ\text{C}$ ,  $di_T/dt = \pm 100\text{ A}/\mu\text{s}$ ,  $V_R = 100\text{ V}$

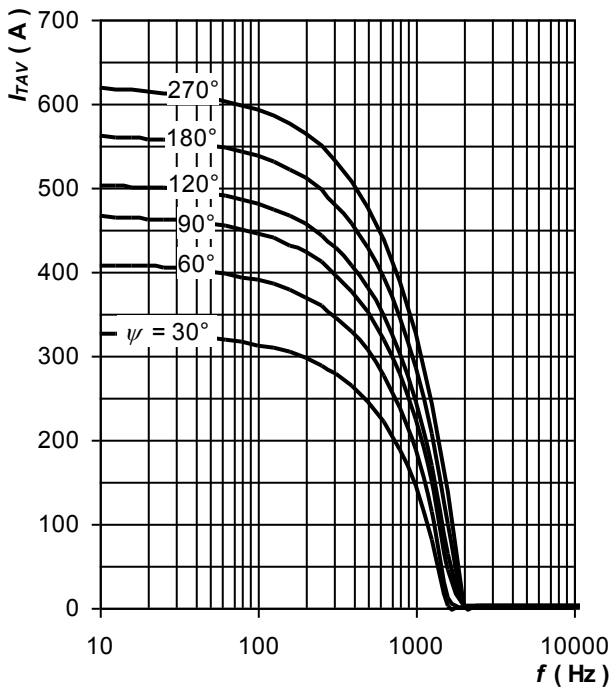


Fig. 23 Average on-state current vs. frequency, trapezoid waveform,  $T_C = 70^\circ\text{C}$ ,  $di_T/dt = \pm 100\text{ A}/\mu\text{s}$ ,  $V_R = 2/3 V_{DRM}$

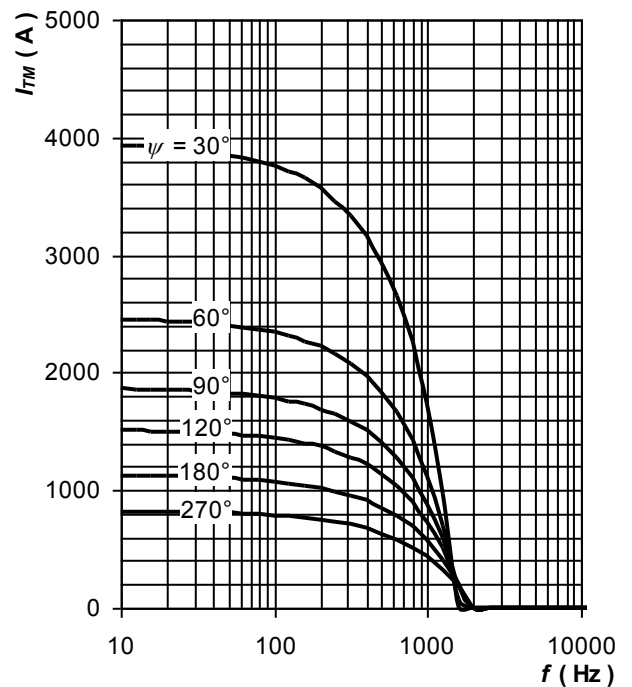


Fig. 24 Maximum on-state current vs. frequency, trapezoid waveform,  $T_C = 70^\circ\text{C}$ ,  $di_T/dt = \pm 100\text{ A}/\mu\text{s}$ ,  $V_R = 2/3 V_{DRM}$

**Frequency Ratings**

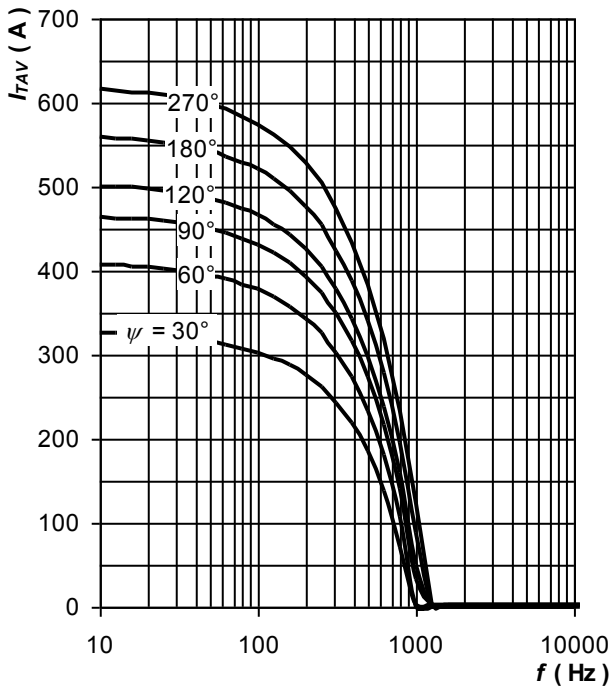


Fig. 25 Average on-state current vs. frequency, trapezoid waveform,  $T_C = 70\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 500\text{ A}/\mu\text{s}$ ,  $V_R = 100\text{ V}$

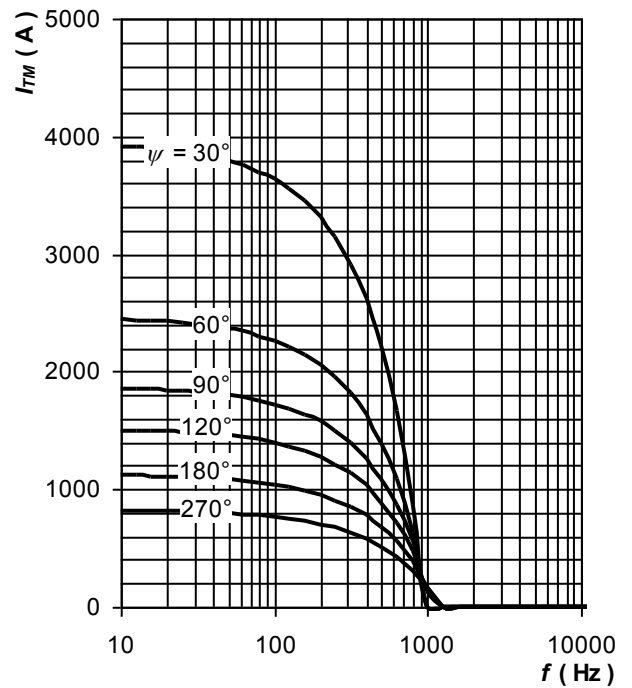


Fig. 26 Maximum on-state current vs. frequency, trapezoid waveform,  $T_C = 70\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 500\text{ A}/\mu\text{s}$ ,  $V_R = 100\text{ V}$

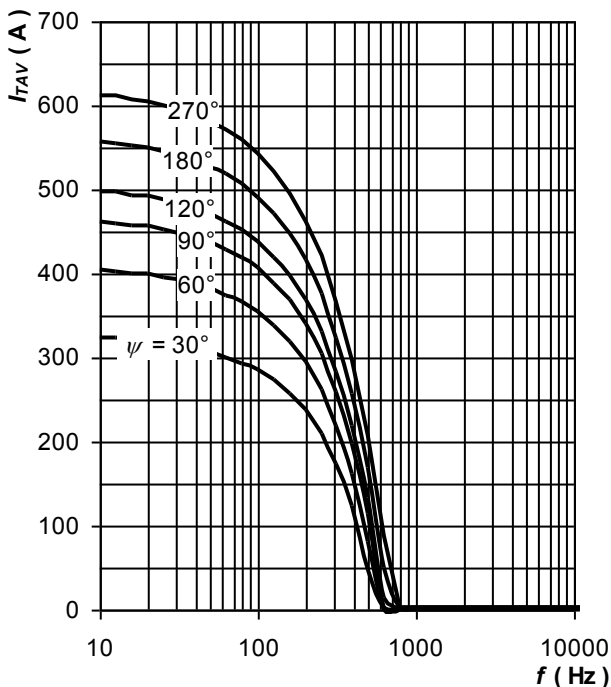


Fig. 27 Average on-state current vs. frequency, trapezoid waveform,  $T_C = 70\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 500\text{ A}/\mu\text{s}$ ,  $V_R = 2/3\text{ }V_{DRM}$

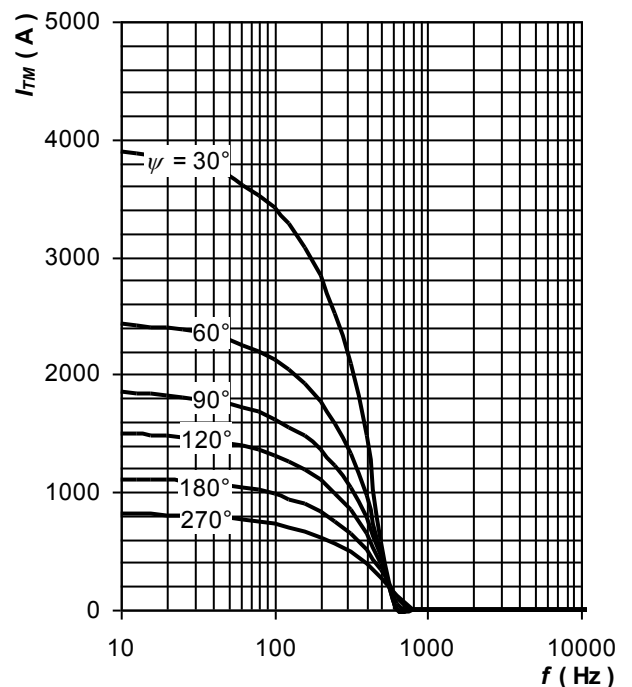


Fig. 28 Maximum on-state current vs. frequency, trapezoid waveform,  $T_C = 70\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 500\text{ A}/\mu\text{s}$ ,  $V_R = 2/3\text{ }V_{DRM}$

**Frequency Ratings**

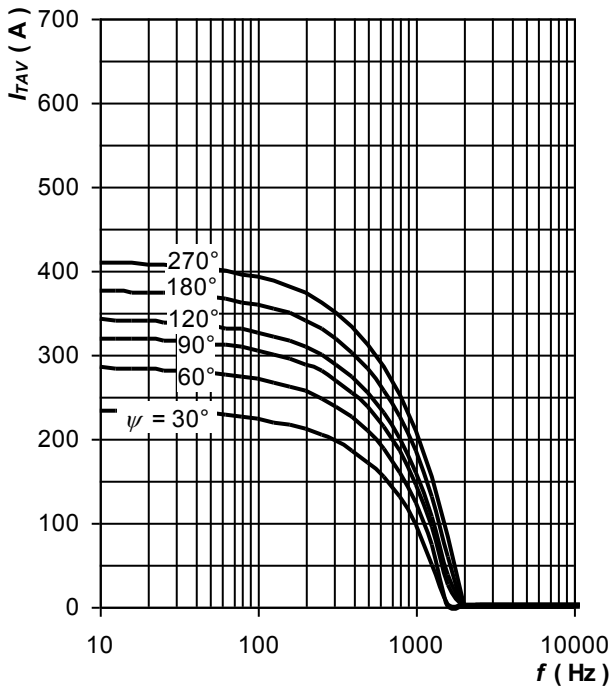


Fig. 29 Average on-state current vs. frequency, trapezoid waveform,  $T_C = 90\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 100\text{ A}/\mu\text{s}$ ,  $V_R = 100\text{ V}$

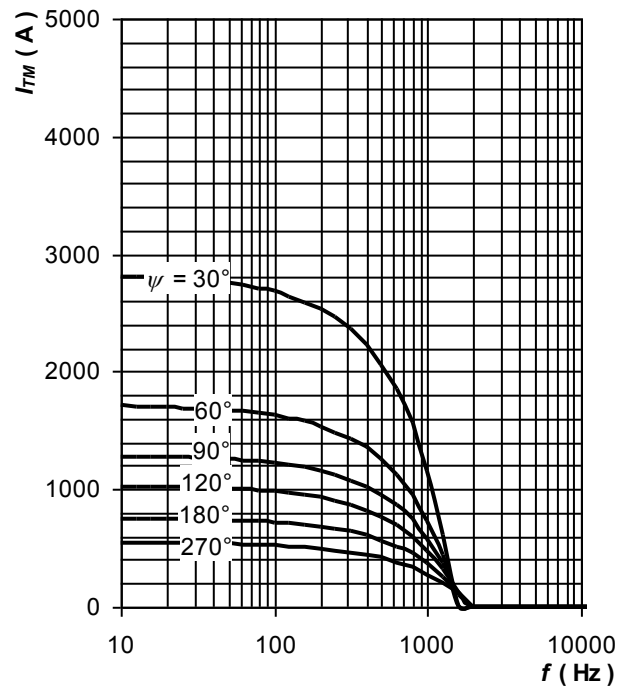


Fig. 30 Maximum on-state current vs. frequency, trapezoid waveform,  $T_C = 90\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 100\text{ A}/\mu\text{s}$ ,  $V_R = 100\text{ V}$

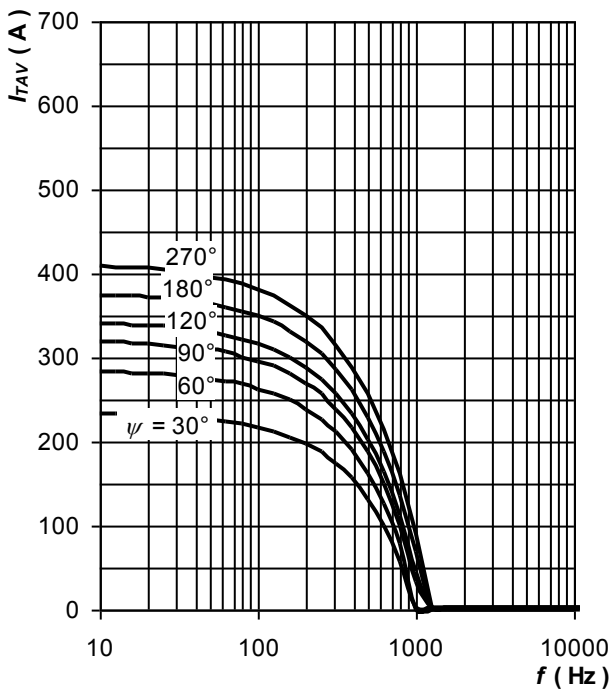


Fig. 31 Average on-state current vs. frequency, trapezoid waveform,  $T_C = 90\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 100\text{ A}/\mu\text{s}$ ,  $V_R = 2/3 V_{DRM}$

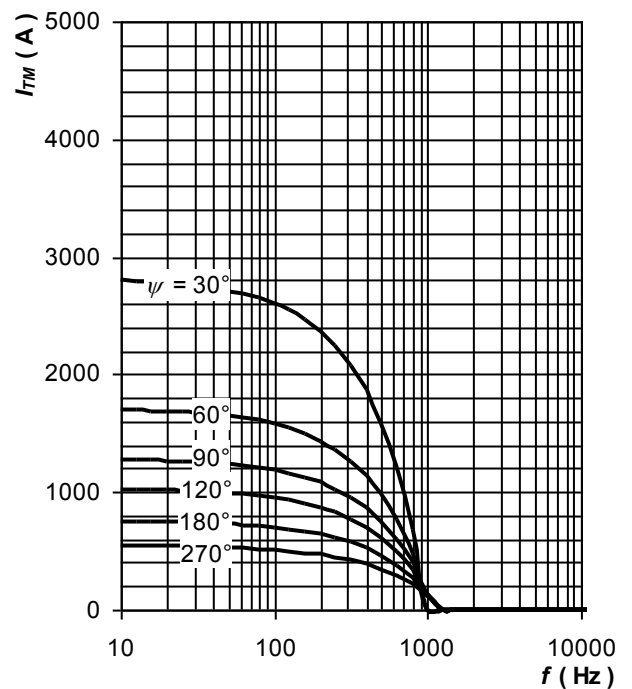


Fig. 32 Maximum on-state current vs. frequency, trapezoid waveform,  $T_C = 90\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 100\text{ A}/\mu\text{s}$ ,  $V_R = 2/3 V_{DRM}$

**Frequency Ratings**

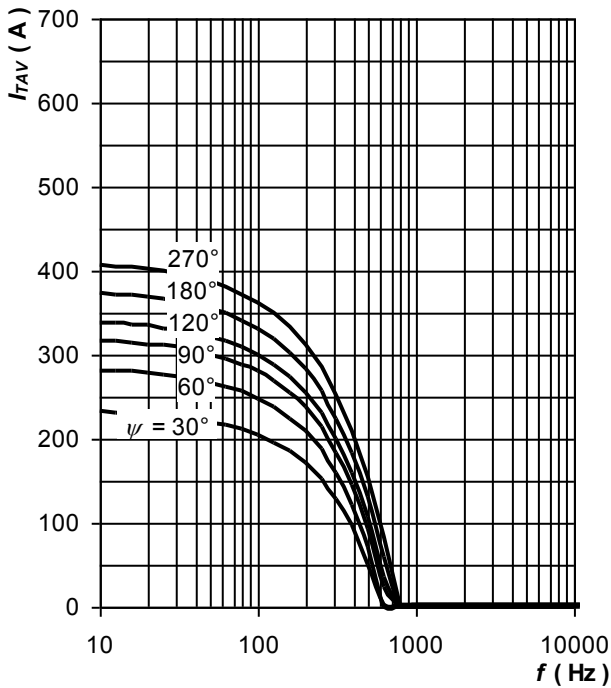


Fig. 33 Average on-state current vs. frequency, trapezoid waveform,  $T_C = 90\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 500\text{ A}/\mu\text{s}$ ,  $V_R = 100\text{ V}$

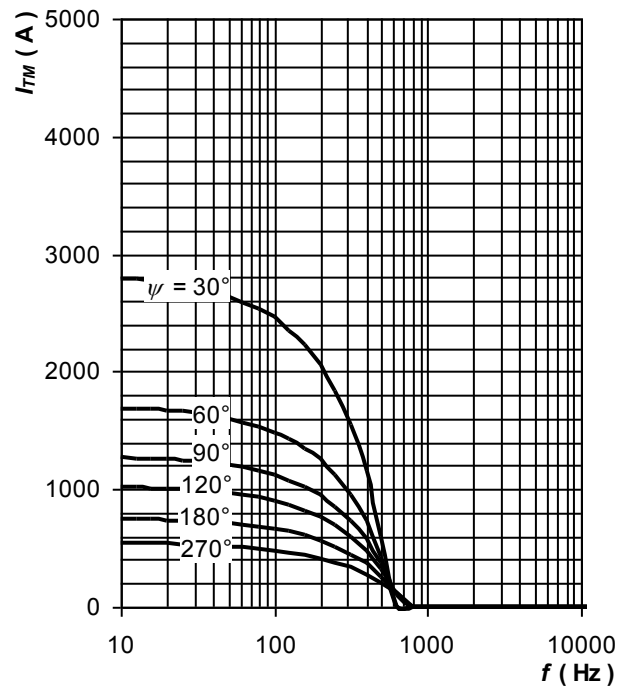


Fig. 34 Maximum on-state current vs. frequency, trapezoid waveform,  $T_C = 90\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 500\text{ A}/\mu\text{s}$ ,  $V_R = 100\text{ V}$

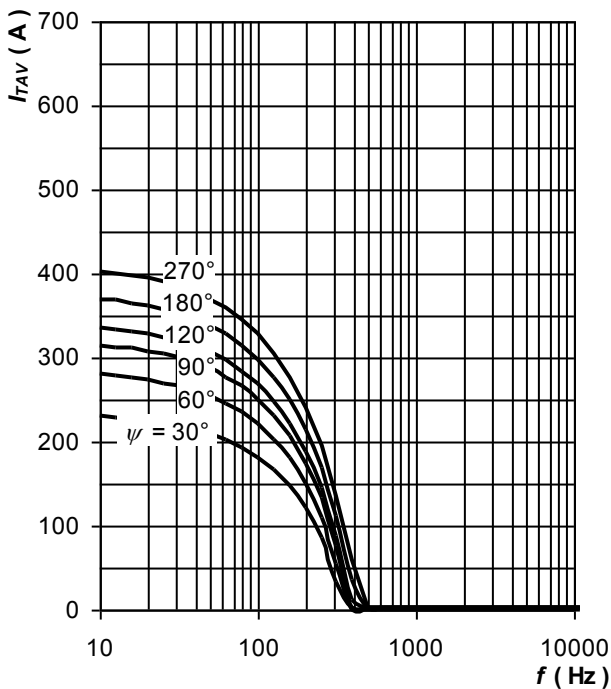


Fig. 35 Average on-state current vs. frequency, trapezoid waveform,  $T_C = 90\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 500\text{ A}/\mu\text{s}$ ,  $V_R = 2/3 V_{DRM}$

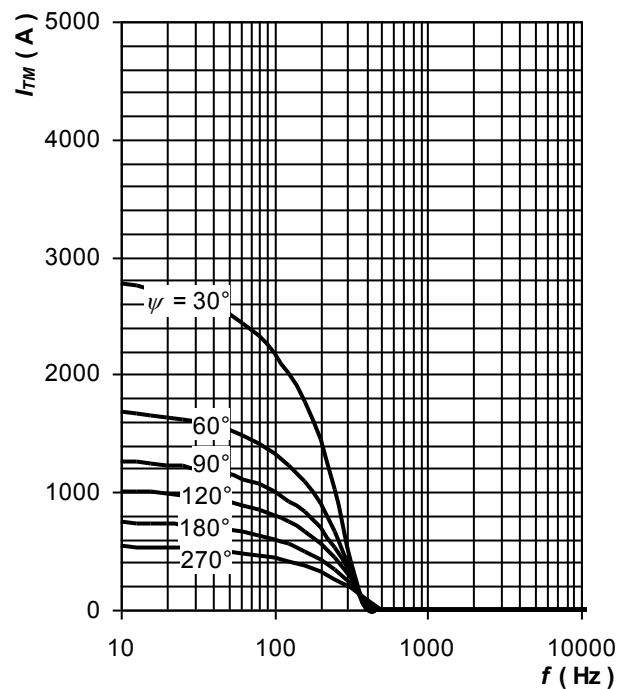


Fig. 36 Maximum on-state current vs. frequency, trapezoid waveform,  $T_C = 90\text{ }^\circ\text{C}$ ,  $di_T/dt = \pm 500\text{ A}/\mu\text{s}$ ,  $V_R = 2/3 V_{DRM}$

Notes:

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ABB s.r.o. reserves the right to change the data contained herein at any time without notice